

Substitute for form 1449A/PTO <h2 style="text-align: center;">INFORMATION DISCLOSURE STATEMENT BY APPLICANT</h2> <p style="text-align: center;">(use as many sheets as necessary)</p>				C mplete if Known Application Number Not Yet Assigned 10/777 755 Filing Date February 13, 2004 First Named Inventor John T. Moore Art Unit Not Yet Assigned 28/3 Examiner Name Not Yet Assigned Thompson Attorney Docket Number M4065.0694/P694-A	
Sheet	1	of	8		

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
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Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ³
		Country Code ² -Number ⁴ -Kind Code ⁵ (if known)				
CAI	BA	WO 97/48032	12/18/1997	Kozicki et al. **		
CAI	BB	WO 99/28914	06/10/1999	Kozicki et al. **		

Examiner Signature		Date Considered	8/27/04
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>		Application Number	Not Yet Assigned 10/777755	
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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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		Filing Date	February 13, 2004	
		First Named Inventor	John T. Moore	
		Group Art Unit	Not Yet Assigned 2813	
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		First Named Inventor	John T. Moore	
		Group Art Unit	Not Yet Assigned- 2813	
		Examiner Name	Not Yet Assigned	
Sheet	8	8	Attorney Docket Number	M4065.0694/P694-A

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	CB6		
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Examiner Signature	Craig A. Thompson	Date Considered	8/27/04
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			Application Number	10/777,755	
			Filing Date	February 13, 2004	
			First Named Inventor	John T. Moore	
			Art Unit	2811 2813	
			Examiner Name	Not Yet Assigned	
Sheet	1	of	3	Attorney Docket Number	M4065.0694/P694-A

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				Art Unit	2814-2813
				Examiner Name	Not Yet Assigned
Sheet	2	of	3	Attorney Docket Number	M4065.0694/P694-A

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